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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/884,670	06/19/2001	Stephen R. Fox	YOR920010104(14270)	4482
75	90 05/19/2004		EXAMINER	
Steven Fischman Esq. Scully Scott Murphy and Presser			POMPEY, RON EVERETT	
400 Garden City			ART UNIT	PAPER NUMBER
Garde City, NY			2812	
	• • •		DATE MAILED: 05/19/200	4

Please find below and/or attached an Office communication concerning this application or proceeding.

,	Application No.	Applicant(s)	
	09/884,670	FOX ET AL.	
Office Action Summary	Examiner	Art Unit	1
	Ron E Pompey	2812	AN
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the	correspondence address	
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1: after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period of the period of the specified above, the maximum statutory period of the specified above and the specified above are specified above. The specified above are specified above as the specified above are specified above. The specified above are specified above as the specified above are specified above. The specified above are specified above as the specified above are specified above. The specified above are specified above as the specified above are specified above. The specified above are specified above as the specified above are specified above. The specified above are specified above as the specified above are specified above. The specified above are specified above are specified above as the specified above are specified above. The specified above are specified above are specified above as the specified above are specified above. The specified above are specified above are specified above are specified above. The specified above are specified above are specified above are specified above. The specified above are specified above are specified above are specified above. The specified above are	36(a). In no event, however, may a reply be ti or within the statutory minimum of thirty (30) da will apply and will expire SIX (6) MONTHS fron cause the application to become ABANDONI	mely filed ys will be considered timely. n the mailing date of this communicatio ED (35 U.S.C. § 133).	n.
Status		•	•
1) Responsive to communication(s) filed on 19 A	<u>oril 2004</u> .		
2a) ☐ This action is FINAL . 2b) ☑ This	action is non-final.	,	
3) Since this application is in condition for allowar	nce except for formal matters, pr	osecution as to the ments i	s
closed in accordance with the practice under E	x parte Quayle, 1935 C.D. 11, 4	53 O.G. 213.	
Disposition of Claims		•	•
		•	
4) Claim(s) <u>1-22,25-36,40 and 48-50</u> is/are pendi			
4a) Of the above claim(s) is/are withdraw	wn from consideration.		
5) Claim(s) is/are allowed.	atad		
6) Claim(s) <u>1-22, 25-36, 40 and 48-50</u> is/are reje	cted.		4
7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/o	r election requirement		
8) Claim(s) are subject to restriction and/o	r ciconon requirement.		
Application Papers		•	•
9) The specification is objected to by the Examine) r.	• .	
10) ☐ The drawing(s) filed on is/are: a) ☐ acc		Examiner.	•
Applicant may not request that any objection to the	drawing(s) be held in abeyance. Se	ee 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the correct	tion is required if the drawing(s) is o	bjected to. See 37 CFR 1.121((d).
11) The oath or declaration is objected to by the Ex	caminer. Note the attached Offic	e Action or form PTO-152.	
Priority under 35 U.S.C. § 119		9	
		-> (-1) (0	•
12) Acknowledgment is made of a claim for foreign	priority under 35 U.S.C. § 119(8	a)-(a) or (t).	
a) ☐ All b) ☐ Some * c) ☐ None of:	a have been received		
1. Certified copies of the priority document		tion No	
2. Certified copies of the priority document3. Copies of the certified copies of the priority			
application from the International Burea		red in this Hational Stage	
* See the attached detailed Office action for a list	· ·	ved.	
	· ·		
	•		•
Attachment(s)		:	
1) Notice of References Cited (PTO-892)	4) Interview Summar	y (PTO-413)	
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail (Date	
Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	5) Notice of Informal 6) Other:	Patent Application (PTO-152)	

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DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 1-22, 25-36, 40 and 48-50 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sadana et al. (US 6,090,689) in further view of Tachimori et al. (US 5,534,446), Sadana et al. (US 5,930,643) and admitted prior art.

Sadana ('689) discloses the steps of:

For claims 1-22 and 25-29:

implanting oxygen ions (14, 18, fig. 2) into a surface of a Si-containing substrate, said implanted oxygen ions having a concentration sufficient to form a buried oxide region during a subsequent annealing step; and

annealing said substrate wherein, said implanted oxygen ions form said buried oxide region (22, fig. 3) (col. 3, Ins. 6-12 and col. 4, In. 8 – col. 5, In. 34).

Sadana ('689) discloses the claimed invention except for:

wherein the annealing step is carried out in an ambient gas comprising at least one high-surface mobility gas that hinders oxide growth;

wherein the annealing step comprises the steps of: partially annealing the substrate so as to form a surface layer of oxygen on the substrate; stripping the surface

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layer of oxygen; and continuing the annealing to complete the formation of said BOX region; and

optically detecting said other defects.

However, Tachimori teaches an annealing step is carried out in an ambient gas comprising at least one high-surface mobility gas that hinders oxide growth (col. 7, ln. 55 – col.8, ln.5) and Sadana('643) teaches partially annealing the substrate so as to form a surface layer of oxygen on the substrate; stripping the surface layer of oxygen; and continuing the annealing to complete the formation of said BOX region (col. 5, lns. 22-43).

Therefore it would have been obvious to those of ordinary skill in the art to combine Tachimori and Sadana ('643) because, the high-surface mobility gas will prevent the semiconductor surface from roughening and that the oxide is of poor quality and needs to be removed before forming a device on the SOI substrate.

Also the admitted prior art (see page 3, lines 1-4) disclose is it well known in the art to use an optical inspection tool to inspect process induced features or defects.

Response to Arguments

3. Applicant's arguments filed 4-19-04, pertaining to claims 1-22, 25-36, 40, 48-50, have been fully considered but they are not persuasive. The applicant argues that "... none of the prior art methods teach or suggest a method in which annealing is carried out until tile or divot defects present at a top surface of said superficial Sicontaining layer are reduced so as to allow optical detection of any other defect that has

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a lower density than the tile or divot defect, and then optically detecting said other defects."

However, since the prior art reads on the **claimed** parameters used to anneal an oxygen-implanted substrate the same results will be achieved as applicants **claimed** invention. Additionally the optically detecting defects; limitation provided in amendment, are addressed in the above rejection.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ron E Pompey whose telephone number is (571) 272-1680. The examiner can normally be reached on flex schedule.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Ron Pompey AU: 2812

May 17, 2004

/John F. Niebling Supervisory Patent Examiner

Technology Center 2800